

SANYO	No.2747	2SK1066
		N-Channel Junction Silicon FET High-Frequency General-Purpose Amp Applications

Applications

- High-frequency general-purpose amp
- AM tuner RF amp
- Low-noise amp

Features

- Large $|y_{fs}|$
- Small c_{rss}
- Very low noise figure
- Very small-sized package permitting 2SK1066-applied sets to be made smaller and slimmer

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	V_{DSX}	15	V
Gate to Drain Voltage	V_{GDS}	-15	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

		min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDS}$ $I_G = -10\mu\text{A}, V_{DS} = 0$	-15			V
Gate Cutoff Current	I_{GSS} $V_{GS} = -10\text{V}, V_{DS} = 0$			-1.0	nA
Cutoff Voltage	$V_{GS(off)}$ $V_{DS} = 5\text{V}, I_D = 100\mu\text{A}$	-0.2	-0.5	-1.5	V
Drain Current	I_{DSS} $V_{DS} = 5\text{V}, V_{GS} = 0$	≈ 3.5		≈ 12.0	mA
Forward Transfer Admittance	$ y_{fs} $ $V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{kHz}$	10	17		mS
Input Capacitance	c_{iss} $V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		7.0		pF
Reverse Transfer Capacitance	c_{rss} $V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		2.0		pF
Noise Figure	NF $V_{DS} = 5\text{V}, R_g = 1\text{k}\Omega, I_D = 1\text{mA}, f = 1\text{kHz}$	1.5			dB

※: The 2SK1066 is classified by I_{DSS} as follows (unit: mA):

3.5	20	6.0	5.0	21	8.5	7.3	22	12.0
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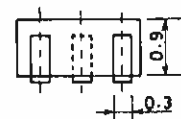
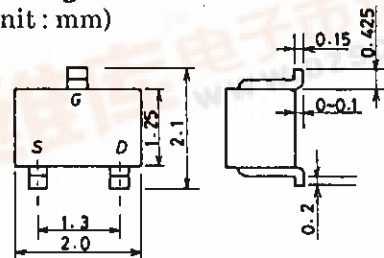
(Note) Marking: A

I_{DSS} rank: 20, 21, 22

• For CP package version, use the 2SK436.

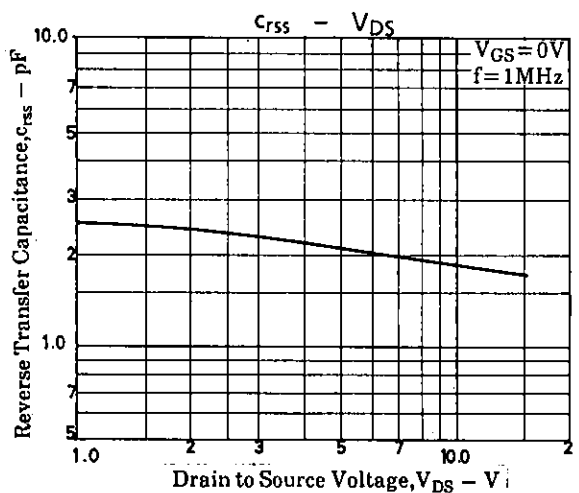
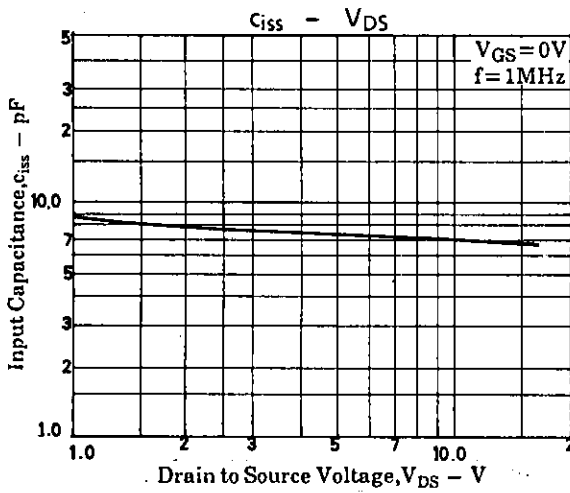
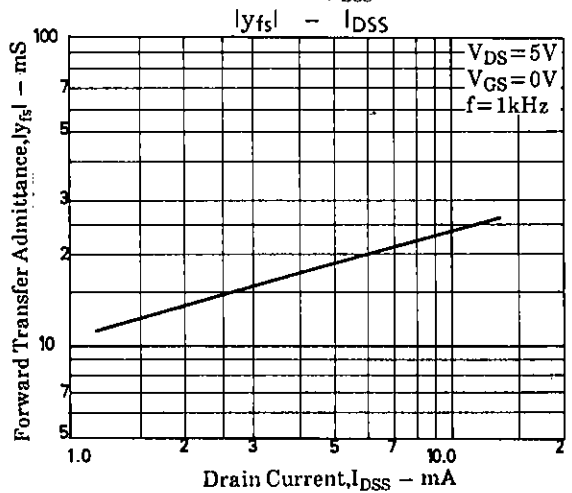
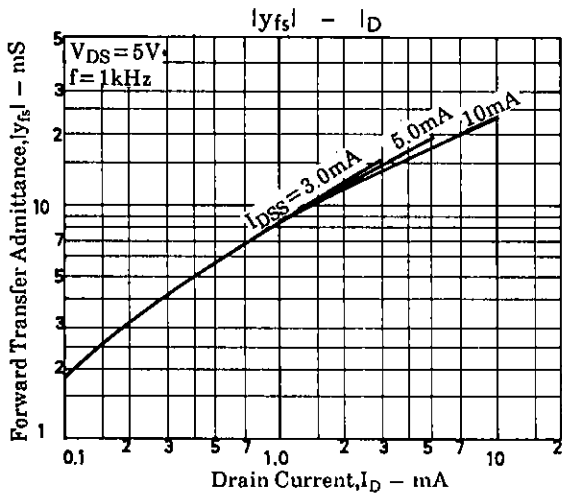
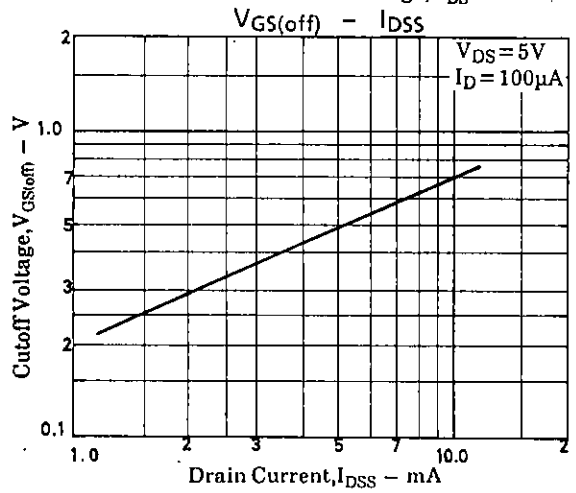
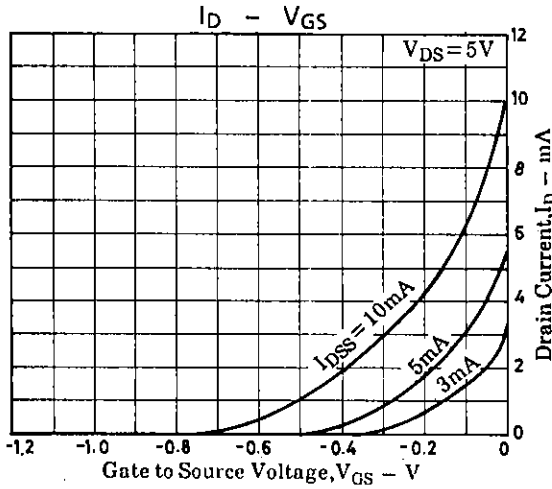
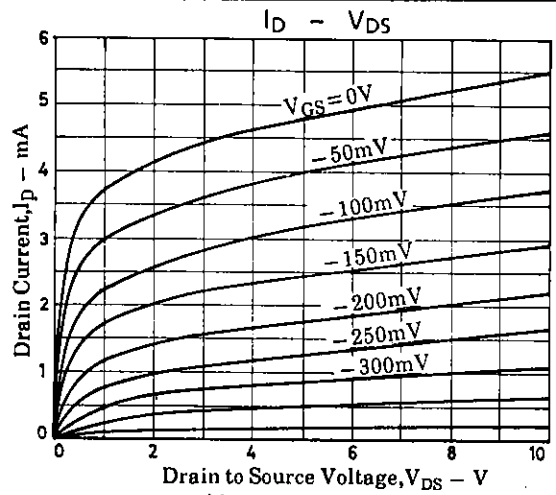
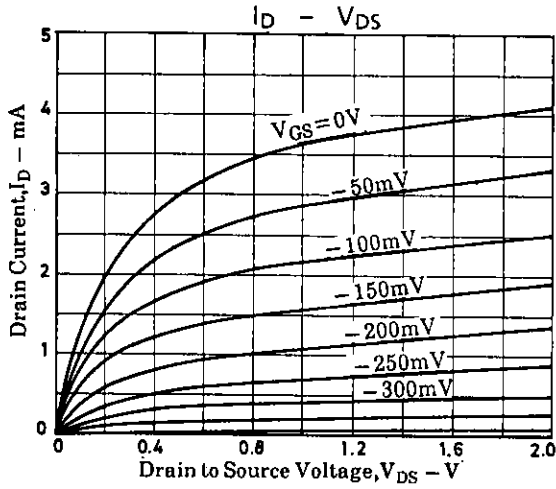
Package Dimensions 2058

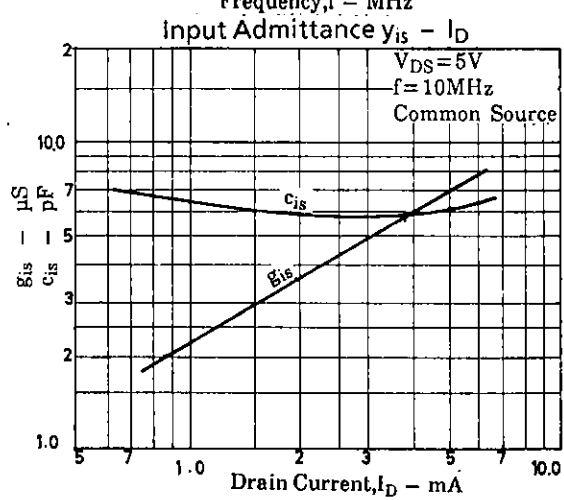
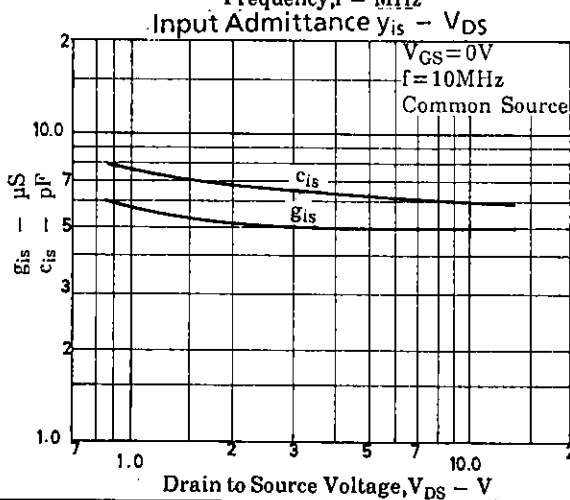
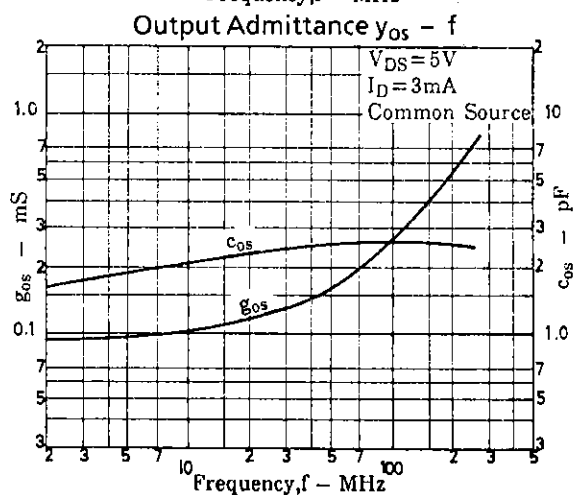
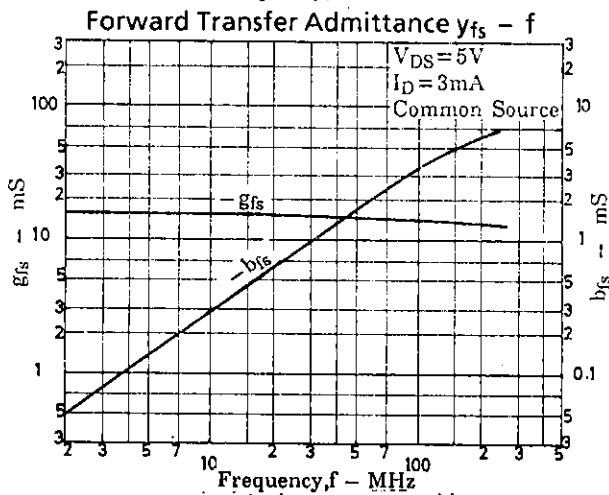
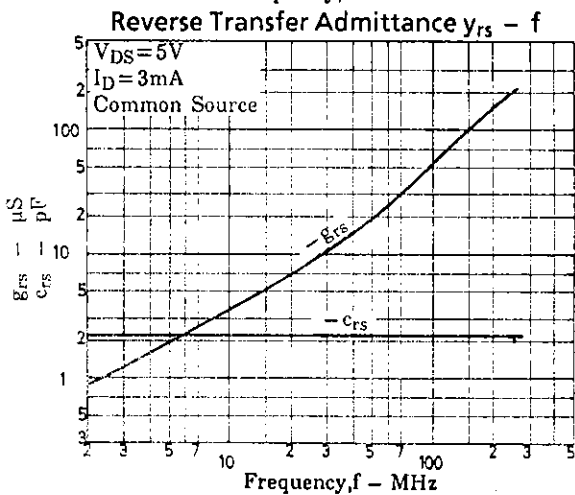
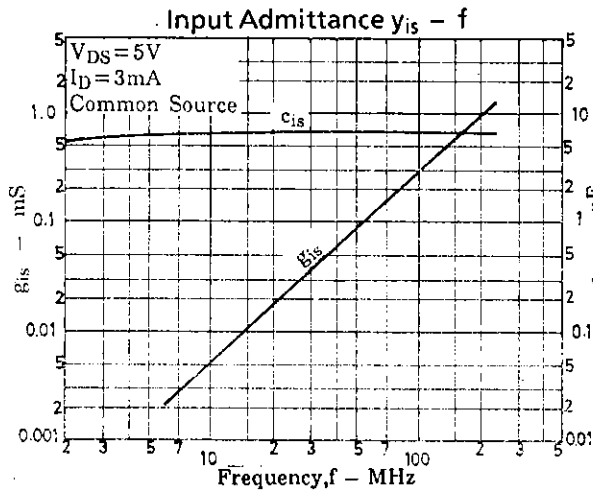
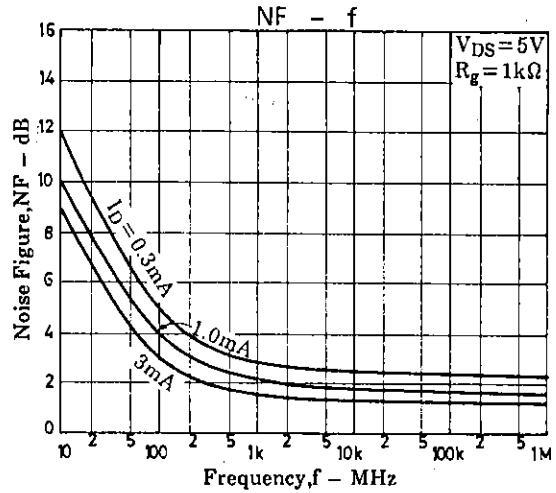
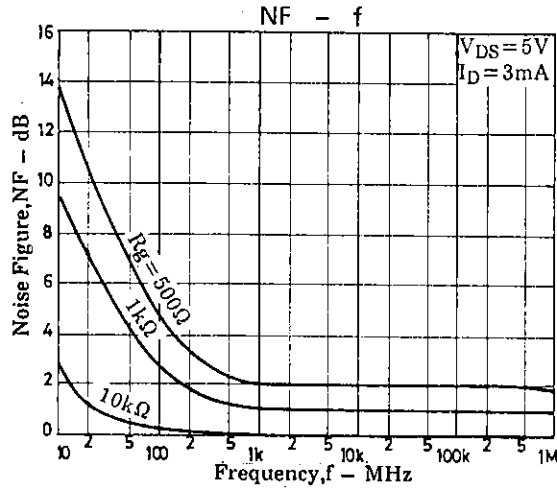
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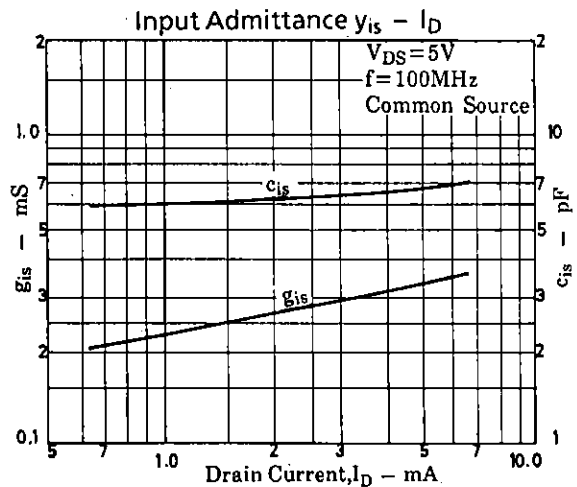
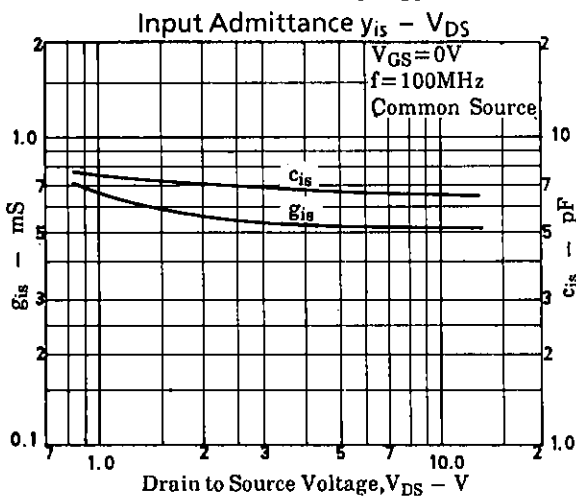
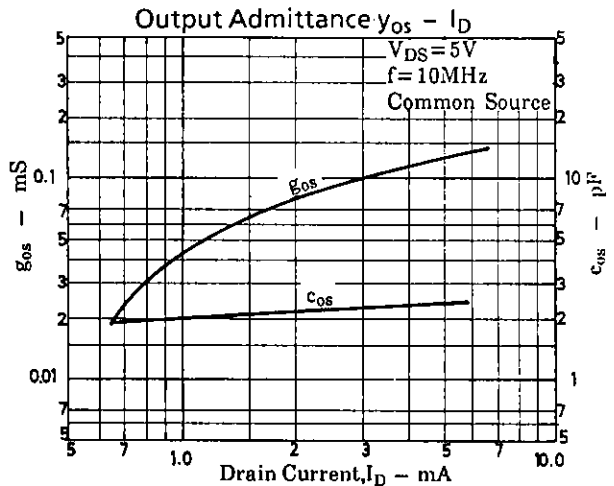
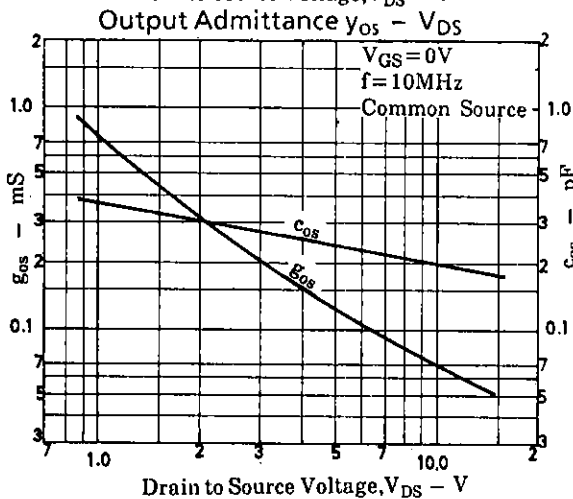
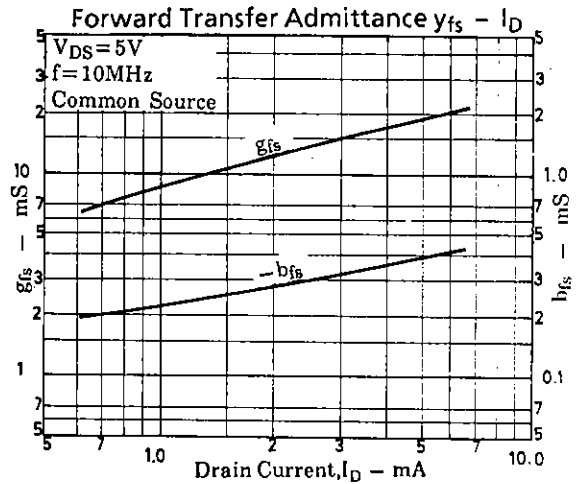
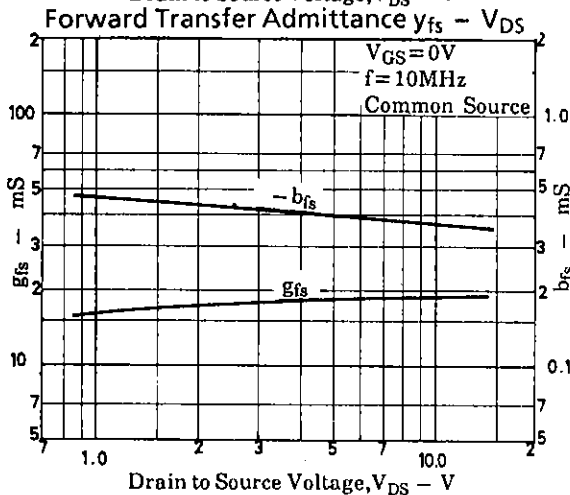
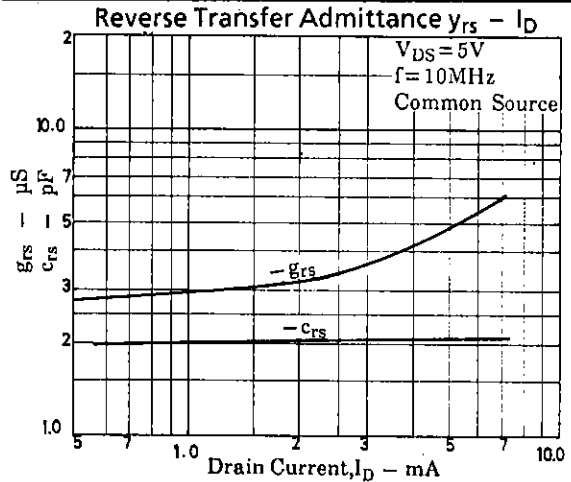
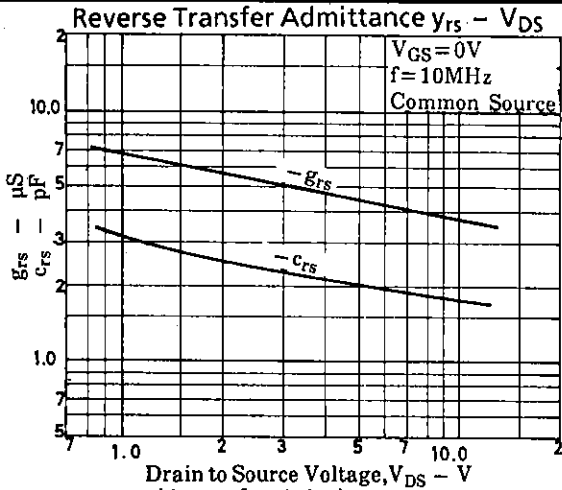


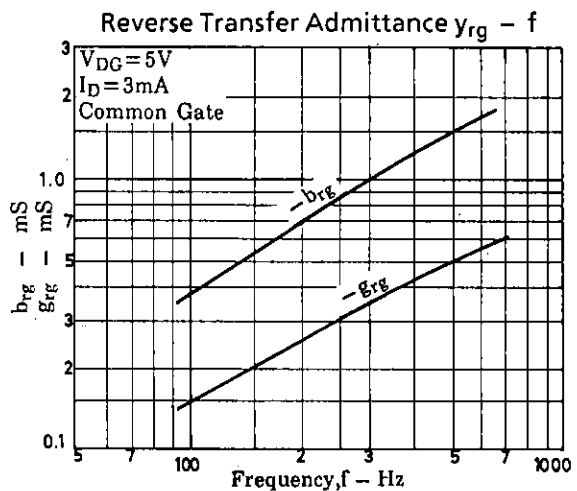
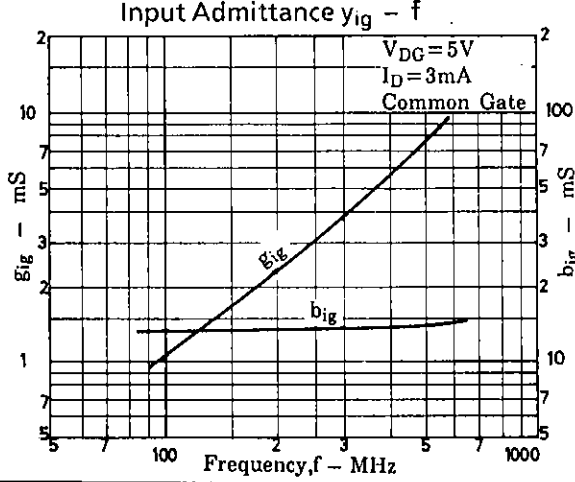
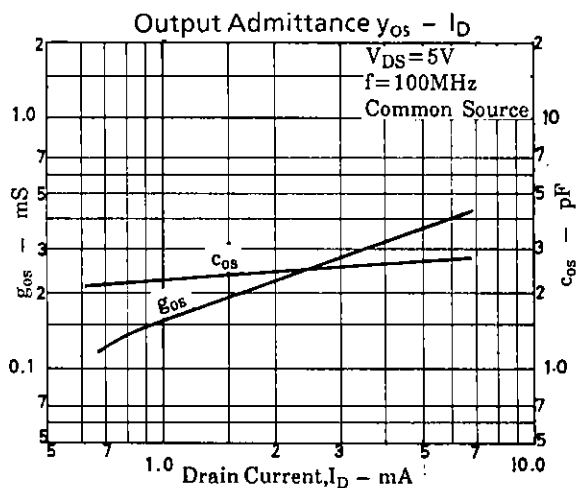
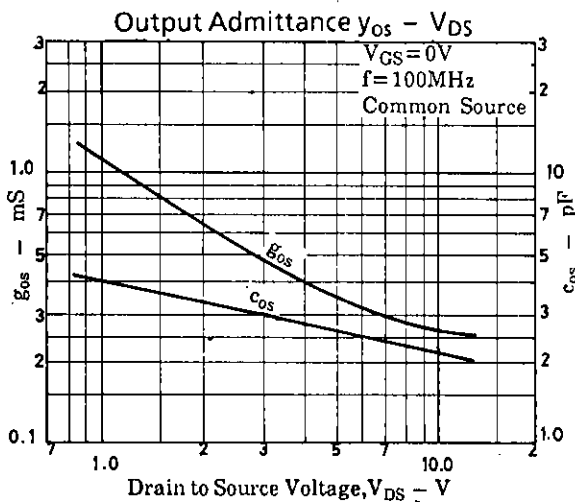
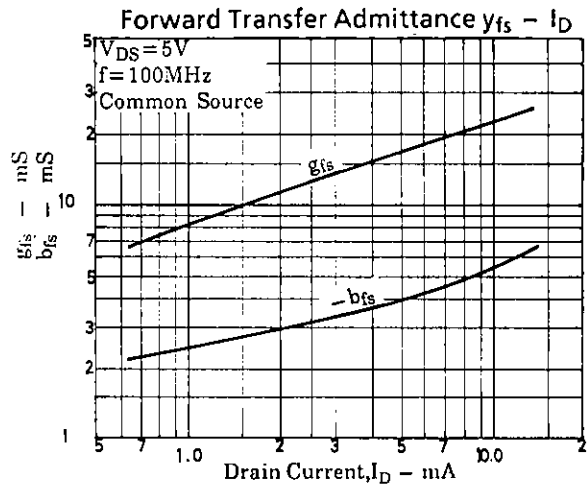
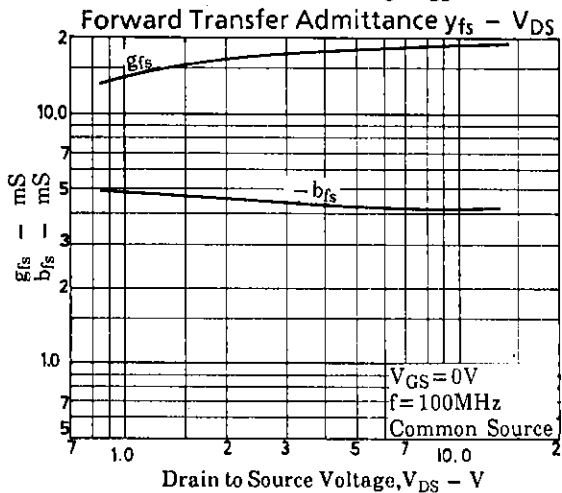
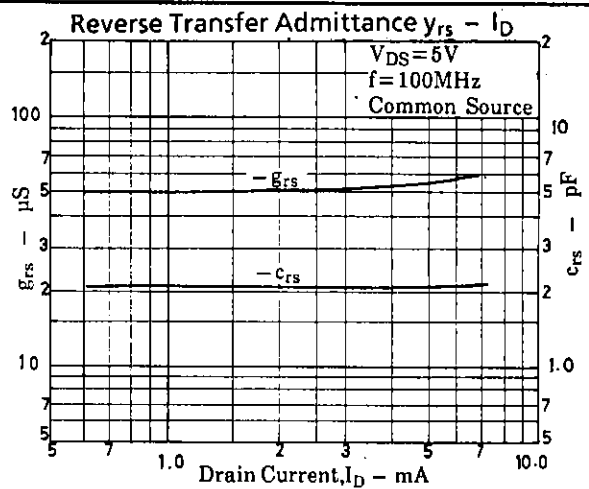
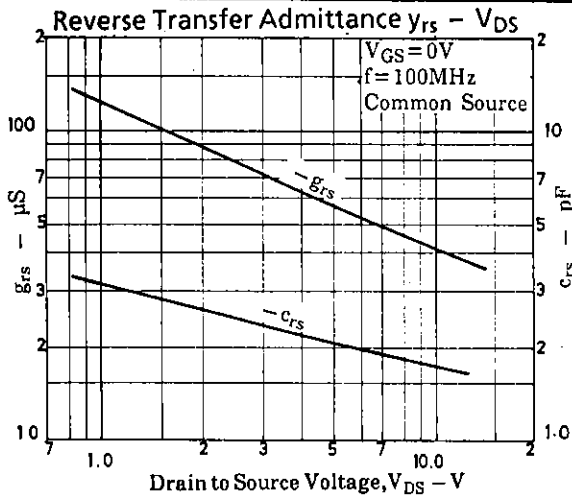
SANYO: MCP
S: Source
G: Gate
D: Drain

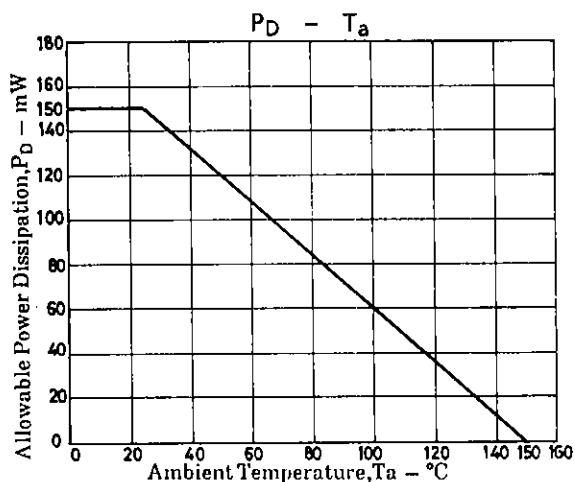
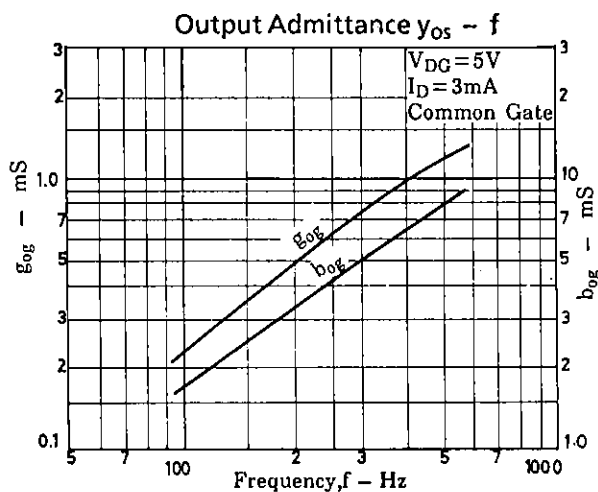
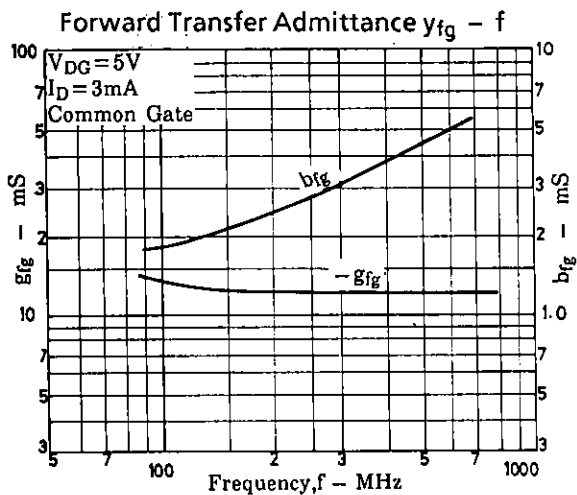












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